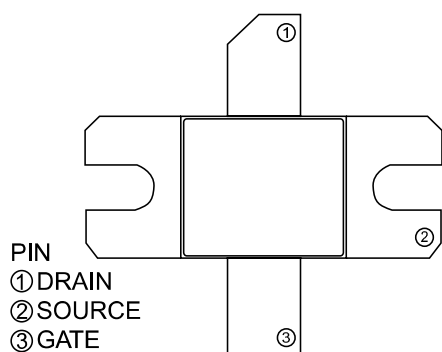


# RD70VHF1 (XE0047)

Nch MOS FET



## ABSOLUTE MAXIMUM RATING

Symbol	Test conditions	Rating	Unit
Pch	Tc=25°C	150	W
VDSS	Vgs=0V	30	V
VGSS	Vds=0V	±20	V
Tj		+175	°C
Tstg		-40 ~ +125	°C

## ELECTRICAL CHARACTERISTIC(Ta=25°C)

Parameter	Symbol	Test conditions	Limits		Unit
			Min	Max	
Saturated drain current	IDSS	Vds=17V, Vgs=0V		300	μA
Gate to source leakage current	IGSS	Vds=10V, Vgs=0V		5	μA
Threshold voltage	Vth	Vds=12V, Ids=1ma	1.3	2.3	V
Output power 1	Po1	f=175MHz, Pin=6W	70		W
Drain efficiency 1	ηD1	Vds=12.5V Ids(idle)=2.0A	55		%
Output power 2	Po2	f=520MHz, Pin=10W Vds=12.5V	50		W
Drain efficiency 2	ηD2	Ids(idle)=2.0A	50		%